SOI-725-1-1-HR

Quality : Prime	**Diameter :** 100 mm [1]

Top silicon layer

Parameters	Measurement equipment /conditions	Min	Target	Max	Unit
Metrology edge exclusion	All parameters			5	**mm**
Mean thickness	+/- 3 sigma	980	1000	1020	**nm**
Doping type / species	P type / Boron				
Resistivity	SEMI M1	8.5		11.5	**Ω.cm**
Crystal orientation	SEMI M1		<100>		

Buried oxide

Parameters	Measurement equipment /conditions	Min	Target	Max	Unit
Mean thickness		900	1000	1100	**nm**

Handle wafer with oxidized backside

Parameters	Measurement equipment /conditions	Min	Target	Max	Unit
Thickness	SEMI M1	710	725	740	**µm**
Doping type / species	N/A				
Resistivity	SEMI M1	750		1000	**Ω.cm**
Crystal orientation	SEMI M1		<100>		

Mechanical

Parameters	Measurement equipment /conditions	Min	Target	Max	Unit
Diameter			100 [1]		**mm**
TTV				5	**µm**
Warp				60	**µm**

[1] This 100mm diameter was obtained by downsizing 200mm wafers. Left-over of various shape/size for piece-part/chip processing is also available.

The downsizing procedure was as follows:

1. Cleanroom open 150mm wafers
2. Blanket coat 5um thick photoresist on each wafer
3. Lasercore wafers
4. Edge grind wafers
5. Laserscribe with original wafer ID (if any)
6. Photoresist strip
7. Cleanroom package and seal